

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLN. OF: ASPAR et al.

SERIAL NO.: 10/784,601

FILED: February 23, 2004

FOR: A Method for Producing a Thin Layer of Semiconductor Material

DOCKET: BREV 12370 CON4

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Dear Sir:

In connection with the above-entitled matter, Applicants hereby proffer U.S. Patent Office Form PTO-1449, including copies of the references listed therein. These references came to applicants' attention in connection with litigation concerning a related U.S. Patent. The claims in the present application are believed to be patentably distinguished over these references.

This Supplemental Information Disclosure Statement is being made pursuant to the duty of disclosure imposed by law and formulated in 37 CFR 1.56(A). No representation is made that the information thus disclosed in fact constitutes prior art or that it is the closest prior art, inasmuch as 37 CFR 1.56(A) relies on a materiality concept which depends on subjectivity.

The enclosed Supplemental Information Disclosure Statement is being submitted prior to issuance of the first action on the merits. Therefore, we believe there are no fees involved with this Information Disclosure Statement. In the event there are any fee deficiencies or additional

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fees are payable, please charge them (or credit any overpayment) to our Deposit Account No. 08-1391.

Respectfully submitted,



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CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on May 10, 2004 at Tucson, Arizona.

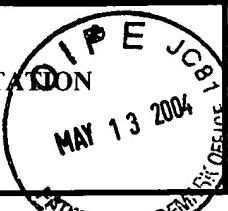
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INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)



Docket Number (Optional)

BREV 12370 CON4

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10/784,601

Applicant(s)

ASPAR et al.

Filing Date

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Group Art Unit

*EXAMINER
INITIAL

OTHER DOCUMENTS (Including Title, Date, Pertinent Pages, Etc.)

"Hydrogen-Related Complexes as the Stressing Species in High-Fluence, Hydrogen-Implanted, Single-Crystal Silicon" Cerofolini et al., *Physical Review B*, Volume 46, Number 4, 1992, pgs. 2061-2070

"Crystallographic Nature and Formation Mechanisms of Highly Irregular Structure in Implanted and Annealed Si Layers" Komarov et al., *Radiation Effects*, Volume 42, 1979, pgs. 169-178

"Observation of Blistering and Amorphization on Germanium Surface After 450 keV Ar+ION Bombardment" Kamada et al, *Radiation Effects*, Volume 28, 1976, pgs. 43-48

"Orientation Dependence of Flaking of Ion Irradiated Aluminum Single Crystals" Ono et al., *Japanese Journal of Applied Physics*, Volume 25, No., 10, 1986, pgs. 1475-1480

"High Fluence Retention of Noble Gases Implanted in Silicon" Wittmaack et al., *Radiation Effects*, Volume 39, 1978, pgs. 81-95

EXAMINER

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